Regulator Family, 400 mA, 2% and 4% Voltage

Description

The NCV4274 and NCV4274A is a precision micro-power voltage regulator with an output current capability of 400 mA available in the DPAK, D2PAK and SOT-223 packages.

The output voltage is accurate within $\pm 2.0\%$ or $\pm 4.0\%$ depending on the version with a maximum dropout voltage of 0.5 V with an input up to 40 V. Low quiescent current is a feature drawing only 150 µA with a 1 mA load. This part is ideal for automotive and all battery operated microprocessor equipment.

The regulator is protected against reverse battery, short circuit, and thermal overload conditions. The device can withstand load dump transients making it suitable for use in automotive environments.

Features

- 2.5, 3.3 V, 5.0 V, 8.5 V, ±2.0% Output Options
- 2.5, 3.3 V, 5.0 V, ±4.0% Output Options
- Low 150 μA Quiescent Current at 1 mA load current
- 400 mA Output Current Capability
- Fault Protection
- +60 V Peak Transient Voltage with Respect to GND
 - -42 V Reverse Voltage
 - Short Circuit
 - · Thermal Overload
- Very Low Dropout Voltage
- NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These are Pb-Free Devices



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MARKING DIAGRAMS



DT SUFFIX CASE 369C



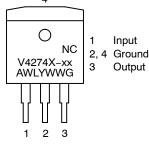
Input 2, 4 Ground

Output

Input

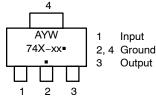


D2PAK **DS SUFFIX** CASE 418AF





SOT-223 ST SUFFIX **CASE 318E**



Х = A or blank

= Voltage Ratings XX

Α = Assembly Location

= Wafer Lot L, WL = Year

WW, W = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 15 of this data sheet.

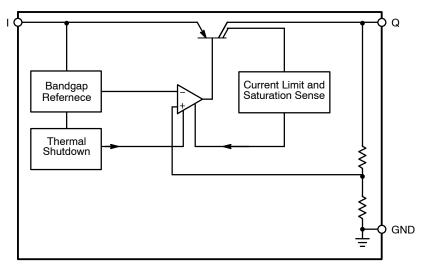


Figure 1. Block Diagram

Pin Definitions and Functions

Pin No.	Symbol	Function				
1	I	Input; Bypass directly at the IC a ceramic capacitor to GND.				
2,4	GND	Ground				
3	Q	Output; Bypass with a capacitor to GND.				

- 1. DPAK 3LD package code 6025
- 2. D2PAK 3LD package code 6083

ABSOLUTE MAXIMUM RATINGS

Pin Symbol, Parameter		Symbol	Condition	Min	Max	Unit
I, Input-to-Regulator	Voltage	VI		-42	45	V
	Current	I _I		Internally Limited	Internally Limited	
I, Input peak Transient Voltage to Regulator with Respect to GND		VI			60	V
Q, Regulated Output	Voltage	V _Q	$V_Q = V_I$	-1.0	40	V
	Current	IQ		Internally Limited	Internally Limited	
GND, Ground Current		I _{GND}		-	100	mA
Junction Temperature Storage Temperature		T _J T _{Stg}		- -50	150 150	°C °C
ESD Capability, Human Body Model		ESD _{HB}		4		kV
ESD Capability, Machine Model		ESD _{MM}		200		V
ESD Capability, Charged Device Model		ESD _{CDM}		1		kV

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

3. This device series incorporates ESD protection and is tested by the following methods:

- - ESD HBM tested per AEC-Q100-002 (EIA/JESD22-A114)
 - ESD MM tested per AEC-Q100-003 (EIA/JESD22-A115)
 - ESD CDM tested per EIA/JES D22/C101, Field Induced Charge Model

OPERATING RANGE

Parameter	Symbol	Condition	Min	Max	Unit
Input Voltage (8.5 V Version)	VI		9.0	40	V
Input Voltage (5.0 V Version)	V _I		5.5	40	V
Input Voltage (3.3 V, and 2.5 V Version)	VI		4.5	40	V
Junction Temperature	TJ		-40	150	°C

THERMAL RESISTANCE

Parameter		Symbol	Condition	Min	Max	Unit
Junction-to-Ambient	DPAK	R _{thja}		-	70 (Note 4)	°C/W
Junction-to-Ambient	D2PAK	R _{thja}		-	60 (Note 4)	°C/W
Junction-to-Case	DPAK	R _{thjc}		-	4	°C/W
Junction-to-Case	D2PAK	R _{thjc}		-	3	°C/W
Junction-to-Tab	SOT-223	Ψ–JLX, ΨLX		-	14.5 (Note 5)	°C/W
Junction-to-Ambient	SOT-223	$R_{\theta JA}, \theta_{JA}$		-	169.7 (Note 5)	°C/W

LEAD FREE SOLDERING TEMPERATURE AND MSL

Parameter		Symbol	Condition	Min	Max	Unit
Lead Free Soldering, (Note 6) Reflow (SMD styles only), Pb-Free		T _{sld}	60s – 150s Above 217s 40s Max at Peak	-	265 pk	°C
Moisture Sensitivity Level		MSL	DPAK and D2PAK SOT-223	1 3	-	

^{6.} Per IPC/JEDEC J-STD-020C

Soldered in, minimal footprint, FR4
 1 oz copper, 5 mm² copper area, FR4

ELECTRICAL CHARACTERISTICS

 $-40^{\circ}C < T_{J} < 150^{\circ}C; \, V_{I}$ = 13.5 V unless otherwise noted.

			Min	Тур	Max	Min	Тур	Max	
Parameter	Symbol	Test Conditions	N	CV427	'4A	ı	NCV42	74	Unit
REGULATOR									
Output Voltage (8.5 V Version)	VQ	5 mA < I _Q < 200 mA 9.5 V < V _I < 40 V	8.33	8.5	8.67	-	-	-	V
Output Voltage (8.5 V Version)	VQ	5 mA < I _Q < 400 mA 9.5 V < V _I < 28 V	8.33	8.5	8.67	-	-	-	V
Output Voltage (5.0 V Version)	VQ	5 mA < I _Q < 400 mA 6 V < V _I < 28 V	4.9	5.0	5.1	4.8	5.0	5.2	V
Output Voltage (5.0 V Version)	VQ	5 mA < I _Q < 200 mA 6 V < V _I < 40 V	4.9	5.0	5.1	4.8	5.0	5.2	V
Output Voltage (3.3 V Version)	VQ	5 mA < I _Q < 400 mA 4.5 V < V _I < 28 V	3.23	3.3	3.37	3.17	3.3	3.43	٧
Output Voltage (3.3 V Version)	VQ	5 mA < I _Q < 200 mA 4.5 V < V _I < 40 V	3.23	3.3	3.37	3.17	3.3	3.43	٧
Output Voltage (2.5 V Version)	VQ	5 mA < I _Q < 400 mA 4.5 V < V _I < 28 V	2.45	2.5	2.55	2.4	2.5	2.6	٧
Output Voltage (2.5 V Version)	VQ	5 mA < I _Q < 200 mA 4.5 V < V _I < 40 V	2.45	2.5	2.55	2.4	2.5	2.6	V
Current Limit	IQ	-	400	600	-	400	600	-	mA
Quiescent Current	I _q	$\begin{split} I_Q &= 1 \text{ mA} \\ V_Q &= 8.5 \text{ V} \\ V_Q &= 5.0 \text{ V} \\ V_Q &= 5.0 \text{ V} \\ V_Q &= 2.5 \text{ V} \\ I_Q &= 250 \text{ mA} \\ V_Q &= 8.5 \text{ V} \\ V_Q &= 5.0 \text{ V} \\ V_Q &= 3.3 \text{ V} \\ V_Q &= 2.5 \text{ V} \\ I_Q &= 400 \text{ mA} \\ V_Q &= 8.5 \text{ V} \\ V_Q &= 5.0 \text{ V} \\ V_Q &= 3.3 \text{ V} \\ V_Q &= 2.5 \text{ V} \\ I_Q &= 400 \text{ mA} \\ V_Q &= 3.3 \text{ V} \\ V_Q &= 2.5 \text{ V} \\ V_Q &= 2.5 \text{ V} \end{split}$	-	195 190 145 140 10 13 12 20 20 30 28	250 250 250 250 250 15 15 20 20 35 35 45	-	- 190 145 140 - 10 13 12 - 20 30 28		μΑ μΑ μΑ μΑ mA mA mA mA mA
Dropout Voltage 8.5 V Version 5.0 V Version 3.3 V Version 2.5 V Version	V_{DR}	$\begin{split} I_Q &= 250 \text{ mA}, \\ V_{DR} &= V_I - V_Q \\ V_I &= 8.5 \text{ V} \\ V_I &= 5.0 \text{ V} \\ V_I &= 4.5 \text{ V} \\ V_I &= 4.5 \text{ V} \end{split}$		250 250 - -	500 500 1.27 2.05	- - -	_ 250 _ _	- 500 1.33 2.1	mV mV V
Load Regulation	ΔV_{Q}	I _Q = 5 mA to 400 mA	-	7	20	_	7	30	mV
Line Regulation	ΔV_{Q}	$\Delta V_I = 12 \text{ V to } 32 \text{ V}$ $I_Q = 5 \text{ mA}$	-	10	25	-	10	25	mV
Power Supply Ripple Rejection	P _{SRR}	fr = 100 Hz, V _r = 0.5 V _{PP}	-	60	-	-	60	-	dB
Temperature output voltage drift	$\Delta V_Q/\Delta T$		-	0.5	-	-	0.5	-	mV/K
Thermal Shutdown Temperature*	T_{SD}	I _Q = 5 mA	165	-	210	165	-	210	°C

^{*}Guaranteed by design, not tested in production

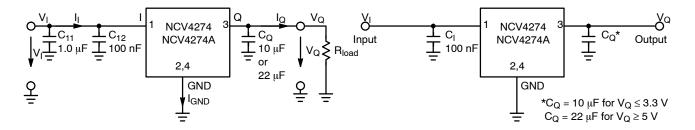


Figure 2. Measuring Circuit

Figure 3. Application Circuit

TYPICAL CHARACTERISTIC CURVES

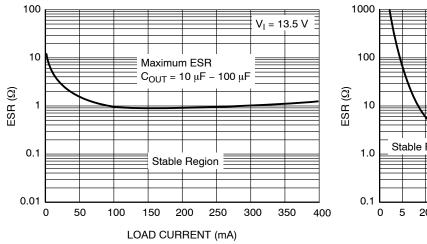


Figure 4. ESR Characterization – 3.3 V, 5 V and 8.5 V Versions

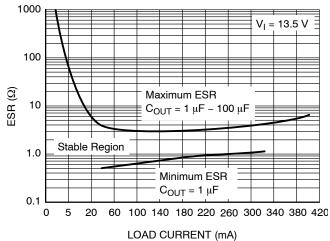
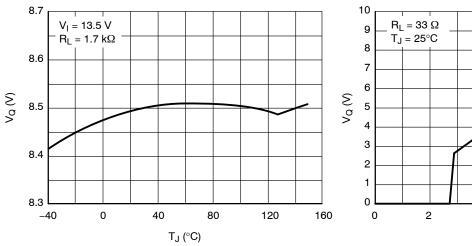


Figure 5. ESR Characterization – 2.5 V Version

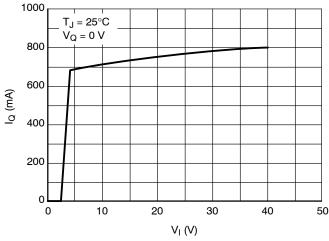
TYPICAL CHARACTERISTIC CURVES - 8.5 V Version



9 R_L = 33 Ω T_J = 25°C 5 5 4 3 2 1 0 0 2 4 6 8 10 V_I (V)

Figure 6. Output Voltage vs. Junction Temperature

Figure 7. Output Voltage vs. Input Voltage



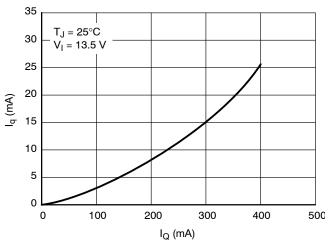
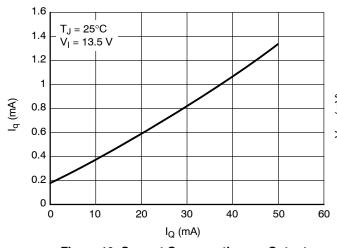


Figure 8. Output Current vs. Input Voltage

Figure 9. Current Consumption vs. Output Current (High Load)



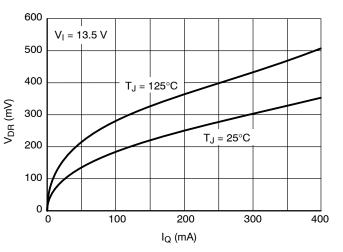
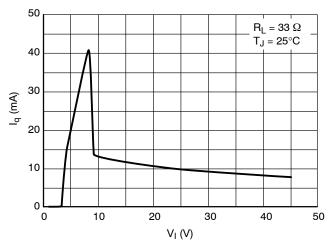


Figure 10. Current Consumption vs. Output Current (Low Load)

Figure 11. Drop Voltage vs. Output Current

TYPICAL CHARACTERISTIC CURVES - 8.5 V Version



 $R_L = 6.8 \text{ k}\Omega$ $T_J = 25^{\circ}C$ 2 0 -2 I_I (mA) -6 -8 -10 -12 -14 -16 -50 -30 -10 10 50 $V_{I}(V)$

Figure 12. Current Consumption vs. Input Voltage

Figure 13. Input Current vs. Input Voltage

TYPICAL CHARACTERISTIC CURVES - 5.0 V Version

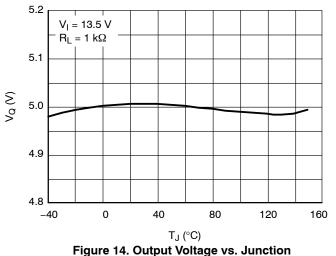


Figure 14. Output Voltage vs. Junction Temperature

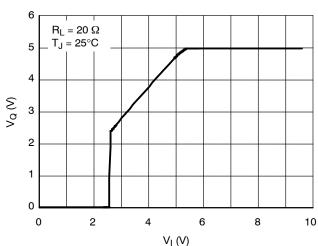


Figure 15. Output Voltage vs. Input Voltage

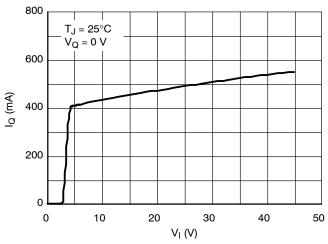


Figure 16. Output Current vs. Input Voltage

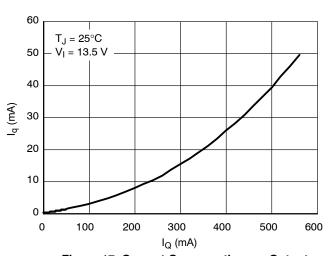


Figure 17. Current Consumption vs. Output Current (High Load)

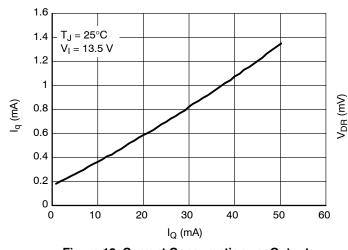


Figure 18. Current Consumption vs. Output Current (Low Load)

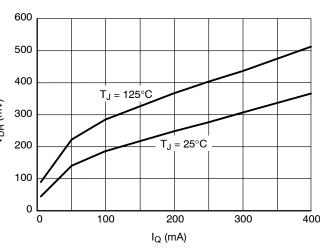
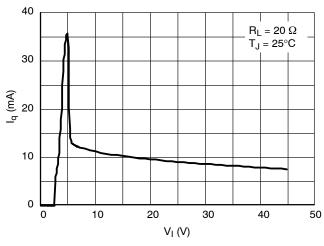


Figure 19. Drop Voltage vs. Output Current

TYPICAL CHARACTERISTIC CURVES - 5.0 V Version



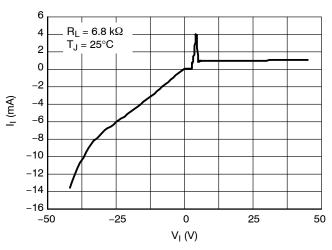
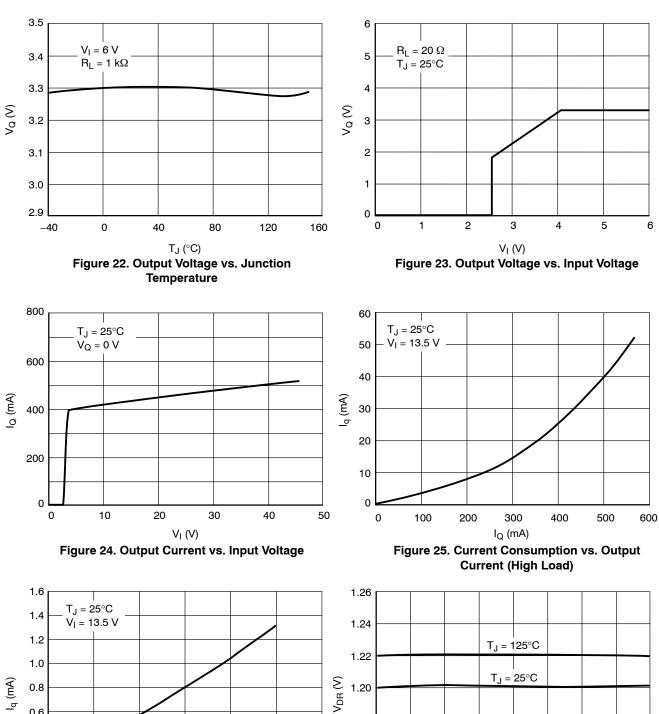


Figure 20. Current Consumption vs. Input Voltage

Figure 21. Input Current vs. Input Voltage

TYPICAL CHARACTERISTIC CURVES - 3.3 V Version



 I_Q (mA) Figure 26. Current Consumption vs. Output **Current (Low Load)**

30

40

50

I_q (mA)

8.0

0.6

0.4

0.2 0

0

10

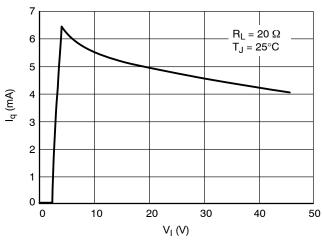
20

 $T_J = 25^{\circ}C$ 1.20 1.18 $V_{DR} = V_{I(min)} - V_{Q}$ 1.16 1.14 100 200 300 400 IQ (mA)

Figure 27. Voltage Drop vs. Output Current

60

TYPICAL CHARACTERISTIC CURVES - 3.3 V Version



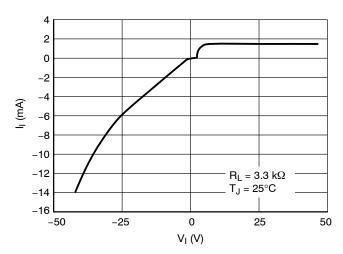
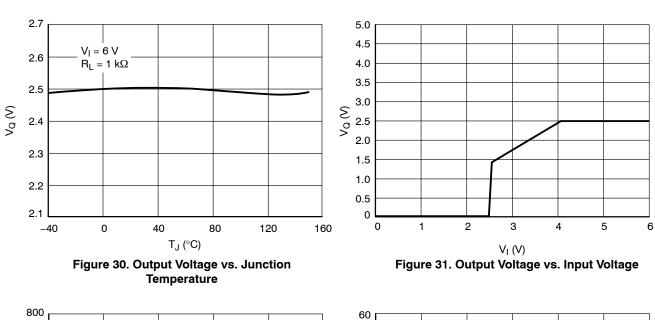
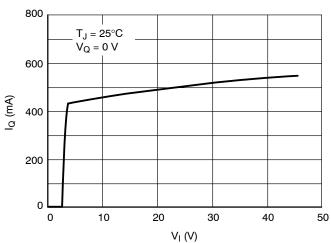


Figure 28. Current Consumption vs. Input Voltage

Figure 29. Input Current vs. Input Voltage

TYPICAL CHARACTERISTIC CURVES - 2.5 V Version







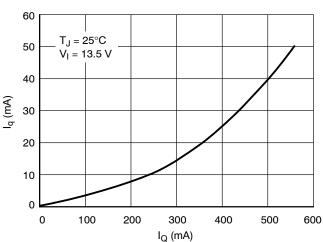


Figure 33. Current Consumption vs. Output Current (High Load)

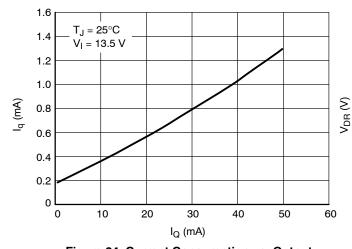


Figure 34. Current Consumption vs. Output Current (Low Load)

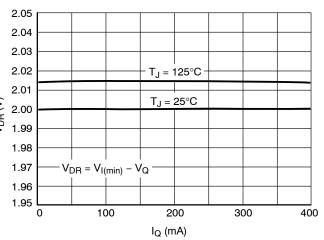
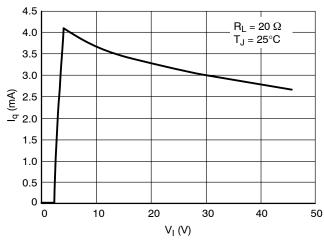


Figure 35. Voltage Drop vs. Output Current

TYPICAL CHARACTERISTIC CURVES - 2.5 V Version



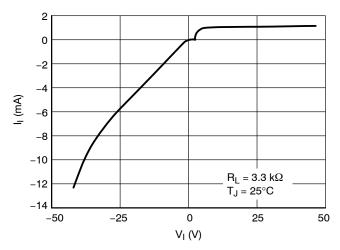


Figure 36. Current Consumption vs. Input Voltage

Figure 37. Input Current vs. Input Voltage

APPLICATION DESCRIPTION

Output Regulator

The output is controlled by a precision trimmed reference and error amplifier. The PNP output has saturation control for regulation while the input voltage is low, preventing over saturation. Current limit and voltage monitors complement the regulator design to give safe operating signals to the processor and control circuits.

Stability Considerations

The input capacitor C_{I1} in Figure 2 is necessary for compensating input line reactance. Possible oscillations caused by input inductance and input capacitance can be damped by using a resistor of approximately 1 Ω in series with C_{I2} .

The output or compensation capacitor helps determine three main characteristics of a linear regulator: startup delay, load transient response and loop stability.

The capacitor value and type should be based on cost, availability, size and temperature constraints. The aluminum electrolytic capacitor is the least expensive solution, but, if the circuit operates at low temperatures (-25°C to -40°C), both the value and ESR of the capacitor will vary considerably. The capacitor manufacturer's data sheet usually provides this information.

The value for the output capacitor C_Q shown in Figure 2 should work for most applications; however, it is not necessarily the optimized solution. Stability is guaranteed at values $C_Q \geq 2.2~\mu F$ and an ESR $\leq 2.5~\Omega$ within the operating temperature range. Actual limits are shown in a graph in the Typical Performance Characteristics section.

Calculating Power Dissipation in a Single Output Linear Regulator

The maximum power dissipation for a single output regulator (Figure 3) is:

$$P_{D(max)} = [V_{I(max)} - V_{Q(min)}]I_{Q(max)} + V_{I(max)}I_{q}$$
 (eq. 1)

Where:

 $V_{I(max)}$ is the maximum input voltage,

V_{Q(min)} is the minimum output voltage,

 $I_{Q(max)}$ is the maximum output current for the application, and

 I_q is the quiescent current the regulator consumes at $I_{O(max)}$.

Once the value of $P_{D(max)}$ is known, the maximum permissible value of $R_{\theta JA}$ can be calculated:

$$\mathsf{P}_{\theta_{\mathsf{JA}}} = \frac{\left(150\;\mathsf{C} - \mathsf{T}_{\mathsf{A}}\right)}{\mathsf{P}_{\mathsf{D}}} \tag{eq. 2}$$

The value of $R_{\theta JA}$ can then be compared with those in the package section of the data sheet. Those packages with $R_{\theta JA}$'s less than the calculated value in Equation 2 will keep the die temperature below 150°C. In some cases, none of the packages will be sufficient to dissipate the heat generated by the IC, and an external heat sink will be required. The current flow and voltages are shown in the Measurement Circuit Diagram.

Heat Sinks

A heat sink effectively increases the surface area of the package to improve the flow of heat away from the IC and into the surrounding air.

Each material in the heat flow path between the IC and the outside environment will have a thermal resistance. Like series electrical resistances, these resistances are summed to determine the value of $R_{\rm BIA}$:

$$R_{\theta JA} = R_{\theta JC} + R_{\theta CS} + R_{\theta SA}$$
 (eq. 3)

Where:

 $R_{\theta JC}$ = the junction-to-case thermal resistance,

 $R_{\theta CS}$ = the case-to-heat sink thermal resistance, and

 $R_{\theta SA}$ = the heat sink-to-ambient thermal resistance.

 $R_{\theta JC}$ appears in the package section of the data sheet.

Like $R_{\theta JA}$, it too is a function of package type. $R_{\theta CS}$ and $R_{\theta SA}$ are functions of the package type, heat sink and the interface between them. These values appear in data sheets of heat sink manufacturers. Thermal, mounting, and heat sinking are discussed in the ON Semiconductor application note AN1040/D, available on the ON Semiconductor Website.

ORDERING INFORMATION4

Device*	Output Voltage Accuracy	Output Voltage	Package	Shipping [†]
NCV4274ADS85R4G	2%	8.5 V	D2PAK (Pb-Free)	800 / Tape & Reel
NCV4274DS50G	4%	5.0 V	D2PAK (Pb-Free)	50 Units / Rail
NCV4274DS50R4G	4%	5.0 V	D2PAK (Pb-Free)	800 / Tape & Reel
NCV4274DT50RKG	4%	5.0 V	DPAK (Pb-Free)	2500 / Tape & Reel
NCV4274ADS50G	2%	5.0 V	D2PAK (Pb-Free)	50 Units / Rail
NCV4274ADS50R4G	2%	5.0 V	D2PAK (Pb-Free)	800 / Tape & Reel
NCV4274ADT50RKG	2%	5.0 V	DPAK (Pb-Free)	2500 / Tape & Reel
NCV4274ST33T3G	4%	3.3 V	SOT-223 (Pb-Free)	4000 / Tape & Reel
NCV4274DT33RKG	4%	3.3 V	DPAK (Pb-Free)	2500 / Tape & Reel
NCV4274AST33T3G	2%	3.3 V	SOT-223 (Pb-Free)	4000 / Tape & Reel
NCV4274ADT33RKG	2%	3.3 V	DPAK (Pb-Free)	2500 / Tape & Reel
NCV4274ADS33R4G	2%	3.3 V	D2PAK (Pb-Free)	800 / Tape & Reel
NCV4274ST25T3G	4%	2.5 V	SOT-223 (Pb-Free)	4000 / Tape & Reel
NCV4274AST25T3G	2%	2.5 V	SOT-223 (Pb-Free)	4000 / Tape & Reel

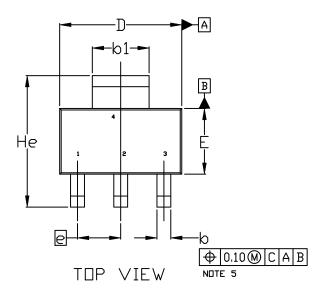
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP

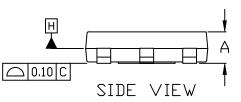
Capable.



SOT-223 (TO-261) CASE 318E-04 ISSUE R

DATE 02 OCT 2018

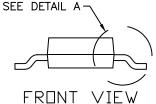




DETAIL A

A1



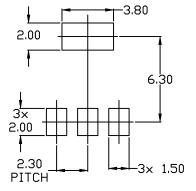




NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: MILLIMETERS
- DIMENSIONS D & E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.200MM PER SIDE.
- 4. DATUMS A AND B ARE DETERMINED AT DATUM H.
- A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT OF THE PACKAGE BODY.
- POSITIONAL TOLERANCE APPLIES TO DIMENSIONS to AND to1.

	MILLIMETERS				
DIM	MIN.	N□M.	MAX.		
Α	1.50	1.63	1.75		
A1	0.02	0.06	0.10		
Ø	0.60	0.75	0.89		
b1	2.90	3.06	3.20		
U	0.24	0.29	0.35		
D	6.30	6.50	6.70		
E	3.30	3.50	3.70		
е		2,30 BSC	,		
١	0.20				
L1	1.50	1.75	2.00		
He	6.70	7.00	7.30		
θ	0°		10°		



RECOMMENDED MOUNTING **FOOTPRINT**

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DESCRIPTION:	SOT-223 (TO-261)		PAGE 1 OF 2	

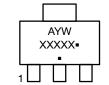
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SOT-223 (TO-261) CASE 318E-04 ISSUE R

DATE 02 OCT 2018

STYLE 1: PIN 1. BASE 2. COLLECTOR 3. EMITTER 4. COLLECTOR	STYLE 2: PIN 1. ANODE 2. CATHODE 3. NC 4. CATHODE	STYLE 3: PIN 1. GATE 2. DRAIN 3. SOURCE 4. DRAIN	STYLE 4: PIN 1. SOURCE 2. DRAIN 3. GATE 4. DRAIN	STYLE 5: PIN 1. DRAIN 2. GATE 3. SOURCE 4. GATE
STYLE 6: PIN 1. RETURN 2. INPUT 3. OUTPUT 4. INPUT	STYLE 7: PIN 1. ANODE 1 2. CATHODE 3. ANODE 2 4. CATHODE	STYLE 8: CANCELLED	STYLE 9: PIN 1. INPUT 2. GROUND 3. LOGIC 4. GROUND	STYLE 10: PIN 1. CATHODE 2. ANODE 3. GATE 4. ANODE
STYLE 11: PIN 1. MT 1 2. MT 2 3. GATE 4. MT 2	STYLE 12: PIN 1. INPUT 2. OUTPUT 3. NC 4. OUTPUT	STYLE 13: PIN 1. GATE 2. COLLECTOR 3. EMITTER 4. COLLECTOR		

GENERIC MARKING DIAGRAM*



A = Assembly Location

Y = Year W = Work

not follow the Generic Marking.

W = Work Week XXXXX = Specific Device Code

= Pb-Free Package

(Note: Microdot may be in either location)
*This information is generic. Please refer to
device data sheet for actual part marking.
Pb-Free indicator, "G" or microdot "•", may
or may not be present. Some products may

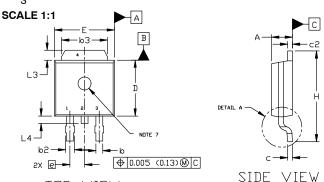
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DESCRIPTION:	SOT-223 (TO-261)		PAGE 2 OF 2	

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DPAK (SINGLE GAUGE) CASE 369C ISSUE G

DATE 31 MAY 2023





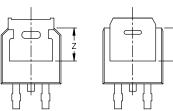
- DIMENSIONING AND TOLERANCING ASME Y14.5M, 1994. CONTROLLING DIMENSION: INCHES
- THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS 63,
- L3. AND Z. L3, AND Z.

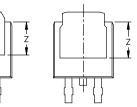
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,
 PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR
 GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
 DIMENSIONS D AND E ARE DETERMINED AT THE
 OUTERMOST EXTREMES OF THE PLASTIC BODY.
 DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
 DETININAL MOLD ESCALUPE.

- OPTIONAL MOLD FEATURE.

DIM	INC	HES	MILLIMETERS		
DIM	MIN.	MAX.	MIN.	MAX.	
Α	0.086	0.094	2.18	2.38	
A1	0.000	0.005	0.00	0.13	
ø	0.025	0.035	0.63	0.89	
b2	0.028	0.045	0.72	1.14	
b 3	0.180	0.215	4.57	5.46	
Ū	0.018	0.024	0.46	0.61	
c2	0.018	0.024	0.46	0.61	
D	0.235	0.245	5.97	6.22	
Ε	0.250	0.265	6.35	6.73	
е	0.090	BSC	5.29 BSC		
Η	0.370	0.410	9.40	10.41	
L	0.055	0.070	1.40	1.78	
L1	0.114	REF	2.90	REF	
L2	0.020	BSC	0.51	BSC	
L3	0.035	0.050	0.89	1.27	
L4		0.040	-	1.01	
Z	0.155		3.93		

TOP VIEW





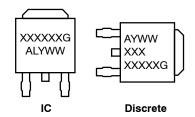
BOTTOM VIEW

2.58

BOTTOM VIEW ALTERNATE

5.80 CONSTRUCTIONS [0.228] 6.20 -L2 GAUGE PLANE [0.244] С Δ1 3.00 [0.102] DETAIL A [0.118] ROTATED 90° CW 1.60 [0.063] 6.17

GENERIC MARKING DIAGRAM*



XXXXXX	= Device Code
Α	= Assembly Location
L	= Wafer Lot
Υ	= Year
WW	= Work Week
G	= Pb-Free Package

*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DUWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

[0.243] RECOMMENDED MOUNTING FOOTPRINT*

STYLE 1: PIN 1. BASE 2. COLLECTOR 3. EMITTER 4. COLLECTOR	STYLE 2:	STYLE 3:	STYLE 4:	STYLE 5:
	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. GATE
	2. DRAIN	2. CATHODE	2. ANODE	2. ANODE
	3. SOURCE	3. ANODE	3. GATE	3. CATHODE
	4. DRAIN	4. CATHODE	4. ANODE	4. ANODE

STYLE 7: PIN 1. GATE 2. COLLECTOR STYLE 6: STYLE 8: STYLE 9: STYLE 10: PIN 1. CATHODE 2. ANODE 3. CATHODE PIN 1. MT1 2. MT2 PIN 1. N/C 2. CATHODE 3. ANODE PIN 1. ANODE 2. CATHODE 3 FMITTER 3 RESISTOR ADJUST 3 GATE 4. COLLECTOR 4. CATHODE 4. ANODE CATHODE

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

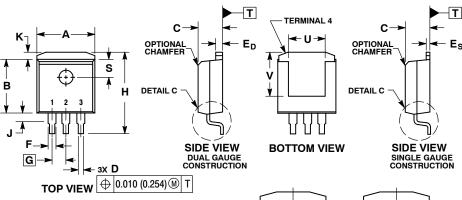
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DESCRIPTION:	DPAK (SINGLE GAUGE)		PAGE 1 OF 1	

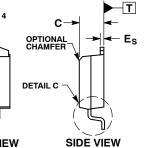
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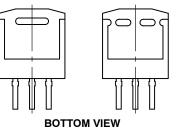


D2PAK CASE 418AF ISSUE E

DATE 15 SEP 2015







OPTIONAL CONSTRUCTIONS

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCHES.
 TAB CONTOUR OPTIONAL WITHIN DIMENSIONS
- DIMENSIONS U AND V ESTABLISH A MINIMUM MOUNTING SURFACE FOR TERMINAL 4.
- DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH OR GATE PROTRUSIONS. MOLD FLASH AND GATE PROTRUSIONS NOT TO EXCEED 0.025 (0.635) MAXIMUM.
- SINGLE GAUGE DESIGN WILL BE SHIPPED AF-TER FPCN EXPIRATION IN OCTOBER 2011.

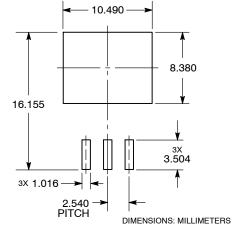
	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.386	0.403	9.804	10.236
В	0.356	0.368	9.042	9.347
С	0.170	0.180	4.318	4.572
D	0.026	0.036	0.660	0.914
E _D	0.045	0.055	1.143	1.397
Es	0.018	0.026	0.457	0.660
F	0.051 REF		1.295 REF	
G	0.100 BSC		2.540 BSC	
Н	0.539	0.579	13.691	14.707
J	0.125 MAX		3.175 MAX	
K	0.050 REF		1.270 REF	
L	0.000	0.010	0.000	0.254
M	0.088	0.102	2.235	2.591
N	0.018	0.026	0.457	0.660
P	0.058	0.078	1.473	1.981
R	0°	8°	0°	8°
S	0.116 REF		2.946 REF	
U	0.200 MIN		5.080 MIN	
٧	0.250 MIN		6.350 MIN	

SOLDERING FOOTPRINT*

DETAIL C

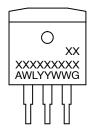
T

SEATING PLANE



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code

= Assembly Location

= Wafer Lot WL YY = Year WW = Work Week G = Pb-Free Package

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DESCRIPTION:	D2PAK		PAGE 1 OF 1

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^{*}This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G", may or not be present.

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